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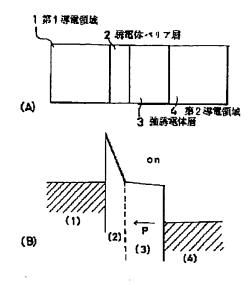
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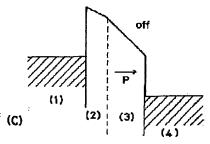
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TITLE

: BISTABLE DIODE





PURPOSE: To provide a bistable diode which has a memory function and a large on/off ratio of a current.

CONSTITUTION: At least two dielectric layers 2 and 3 are provided between a first conductive electrode 1 and a second conductive electrode 4. At least one of the dielectric layers 2 and 3 is a ferroelectric layer (for instance 3). In this construction, a barrier which prevents carriers from moving may be provided along a boundary between the dielectric layer 2 or 3 and at least one of the first and second conductive electrodes 1 and 4. Further, at least one of the first and second conductive electrodes 1 and 4 may be made of metal or oxide material showing superconducting properties.

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